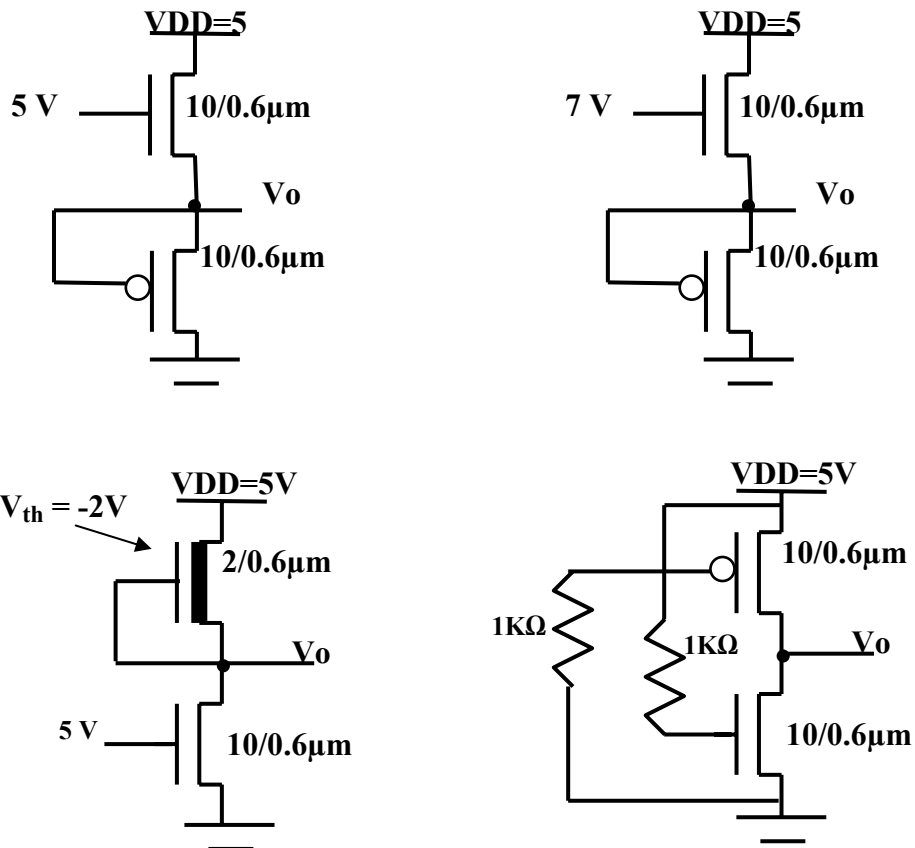


COE360 – Assignment # 3
Dr. M. Elrabaa (061)

Q1) For the circuits shown, assume $V_{tn} = |V_{tp}| = 0.8V$ for the enhancement MOS, and make any other reasonable assumptions you need to find V_o . [5 marks]

Hint: In all circuits, the current through the top device equal that of the bottom one!
 $C_{ox} = 2 \text{ fF}/\mu\text{m}^2$ (i.e. $2E-7 \text{ F}/\text{cm}^2$), $\mu_n = 600$ and $\mu_p = 300$



Q2)

- 1. Design an NMOS inverter using the 0.6µm, 5V technology (parameters above) with the following specifications: [5 marks]**

$V_{OH} = 5 \text{ V}$, $V_{OL} = 0.05V_{DD}$ and maximum input frequency of 250 MHz at a load capacitance of 100 fF.

- 2. For your inverter, calculate:**
 - a. The noise margins,**
 - b. Average static power,**
 - c. and the input frequency at which the average dynamic power would equal the average static power**